

**8A, 60V, 0.300 Ohm, ESD Rated, Logic Level, P-Channel Power MOSFET**

These products are P-Channel power MOSFETs manufactured using the MegaFET process. This process, which uses feature sizes approaching those of LSI circuits, gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use in applications such as switching regulators, switching converters, motor drivers, and relay drivers. These transistors can be operated directly from integrated circuits.

Formerly developmental type TA49203.

**Ordering Information**

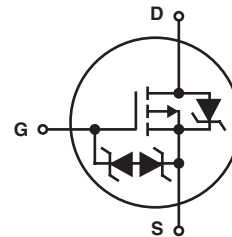
PART NUMBER	PACKAGE	BRAND
RFD8P06LE	TO-251AA	F8P6LE
RFD8P06LESM	TO-252AA	F8P6LE
RFP8P06LE	TO-220AB	FP8P06LE

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-252AA variant in the tape and reel, i.e., RFD8P06LESM9A.

**Features**

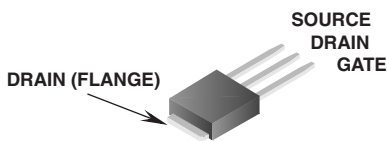
- 8A, 60V
- $r_{DS(ON)} = 0.300\Omega$
- 2kV ESD Protected
- Temperature Compensating PSPICE® Model
- PSPICE Thermal Model
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- 175°C Operating Temperature

**Symbol**

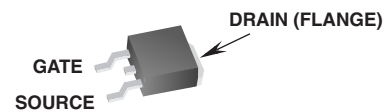


**Packaging**

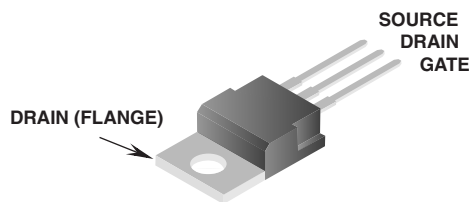
JEDEC TO-251AA



JEDEC TO-252AA



JEDEC TO-220AB



# RFD8P06LE, RFD8P06LESM, RFP8P06LE

## Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ Unless Otherwise Specified

	RFD8P06LE, RFD8P06LESM, RFP8P06LE	UNITS
Drain to Source Voltage	-60	V
Drain to Gate Voltage ( $R_{GS} = 20k\Omega$ )	-60	V
Continuous Drain Current		
$T_C = 25^\circ\text{C}$	-8	A
$T_C = 100^\circ\text{C}$	-6.3	A
Pulsed Drain Current	See Figure 5	
Gate to Source Voltage	$\pm 10$	V
Maximum Power Dissipation	48	W
Dissipation Derating Factor	0.32	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy Rating	See Figure 6	
Operating and Storage Temperature	-55 to 175	$^\circ\text{C}$
Maximum Lead Temperature for Soldering (0.063in (1.6mm) from case for 10s)	300	$^\circ\text{C}$

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

**NOTE:**

1.  $T_J = 25^\circ\text{C}$  to  $150^\circ\text{C}$ .

## Electrical Specifications $T_C = 25^\circ\text{C}$ Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
Drain to Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$ (Figure 11)	-60	-	-	V	
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$ (Figure 12)	-1	-	-2	V	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -60\text{V}$ , $V_{GS} = 0\text{V}$	$T_J = 25^\circ\text{C}$	-	-	-1	$\mu\text{A}$
			$T_J = 150^\circ\text{C}$	-	-	-50	$\mu\text{A}$
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 10\text{V}$	-	-	$\pm 10$	$\mu\text{A}$	
On Resistance (Note 1)	$r_{DS(ON)}$	$I_D = 8\text{A}$ , $V_{GS} = -5\text{V}$ (Figure 9, 10)	-	-	0.300	$\Omega$	
		$I_D = 8\text{A}$ , $V_{GS} = -4.5\text{V}$ (Figure 9, 10)	-	-	0.330	$\Omega$	
Turn-On Time	$t_{ON}$	$V_{DD} = -30\text{V}$ , $I_D \cong 8\text{A}$ , $R_{GS} = 9.1\Omega$ , $R_L = 3.75\Omega$ (Figure 13)	-	-	90	ns	
Turn-On Delay Time	$t_{d(ON)}$		-	10	-	ns	
Rise Time	$t_r$		-	50	-	ns	
Turn-Off Delay Time	$t_{d(OFF)}$		-	30	-	ns	
Fall Time	$t_f$		-	20	-	ns	
Turn-Off Time	$t_{OFF}$		-	-	75	ns	
Total Gate Charge	$Q_{g(TOT)}$		$V_{GS} = 0$ to $-10\text{V}$	-	25	30	nC
Gate Charge at -5V	$Q_{g(-5)}$	$V_{GS} = 0$ to $-5\text{V}$	-	15	18	nC	
Threshold Gate Charge	$Q_{g(TH)}$	$V_{GS} = 0$ to $-1\text{V}$	-	1.2	1.5	nC	
Input Capacitance	$C_{ISS}$	$V_{DS} = -25\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$ (Figure 15)	-	675	-	pF	
Output Capacitance	$C_{OSS}$		-	175	-	pF	
Reverse Transfer Capacitance	$C_{RSS}$		-	50	-	pF	
Thermal Resistance Junction to Case	$R_{\theta JC}$		-	-	3.125	$^\circ\text{C/W}$	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-251AA, TO-252AA	-	-	100	$^\circ\text{C/W}$	
		TO-220AB	-	-	80	$^\circ\text{C/W}$	

## Source to Drain Diode Specifications $T_C = 25^\circ\text{C}$ Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage (Note 1)	$V_{SD}$	$T_J = 25^\circ\text{C}$ , $I_{SD} = -8\text{A}$ , $V_{GS} = 0\text{V}$	-	-	-1.5	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25^\circ\text{C}$ , $I_{SD} = -8\text{A}$ , $di_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	125	ns

**NOTE:**

2. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

Typical Performance Curves Unless Otherwise Specified

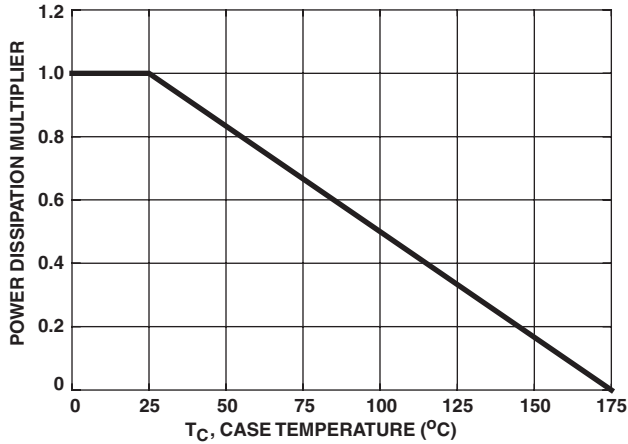


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

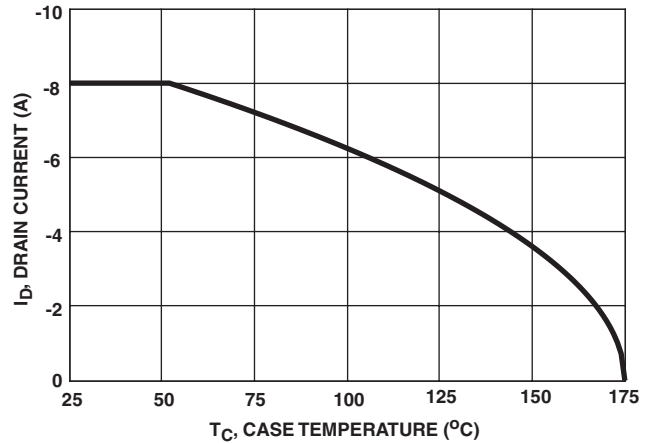


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

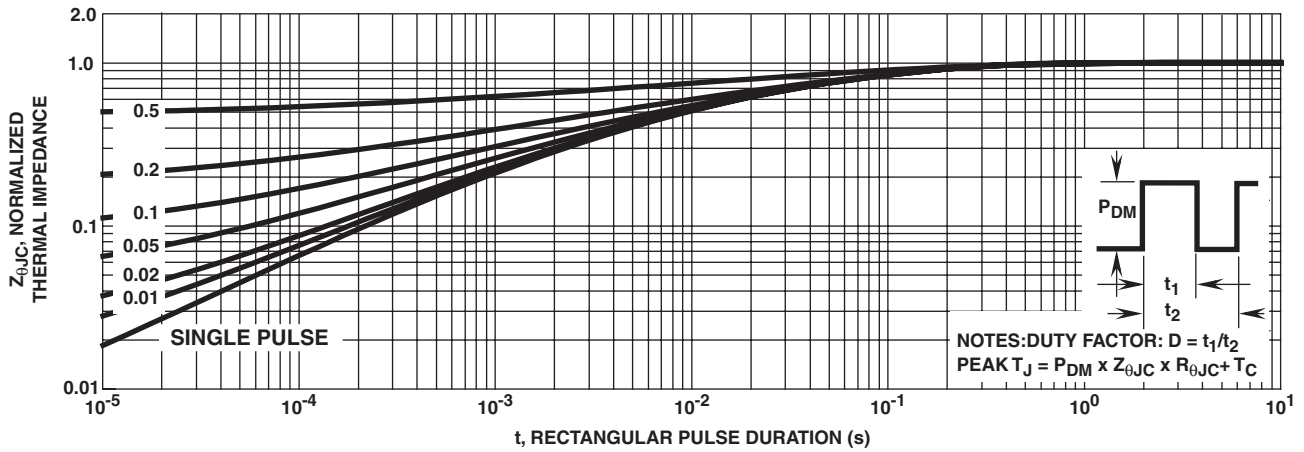


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

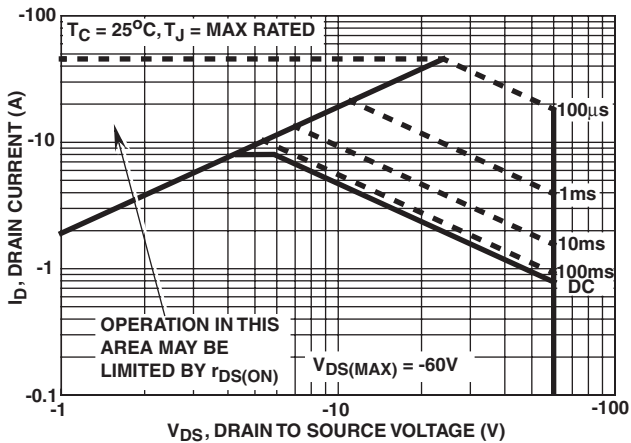


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

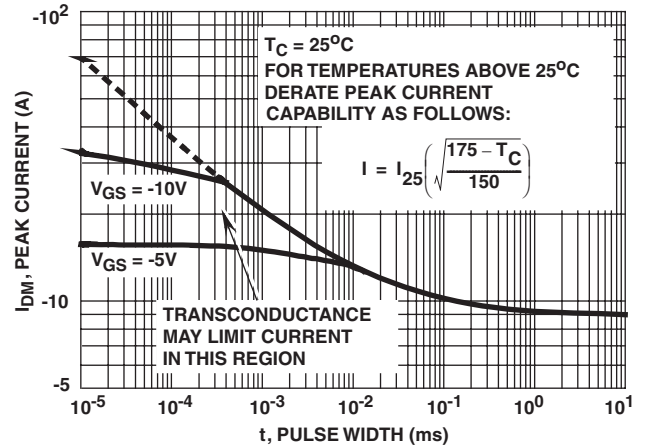
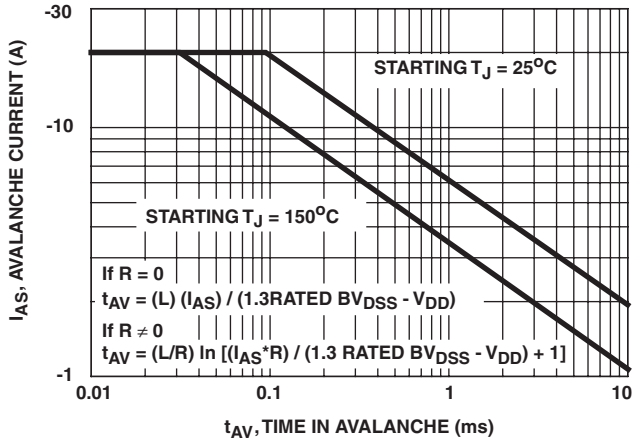
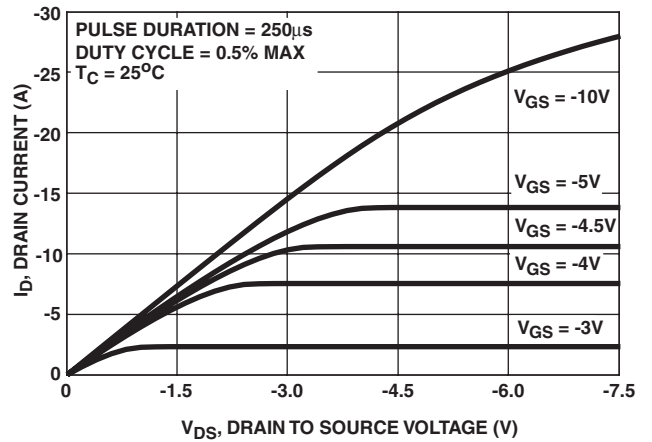


FIGURE 5. PEAK CURRENT CAPABILITY

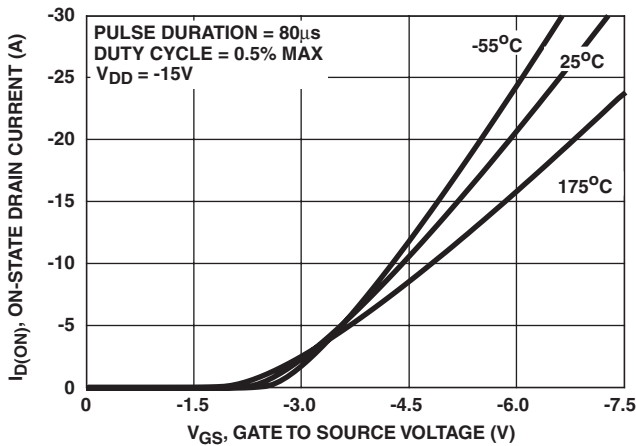
**Typical Performance Curves** Unless Otherwise Specified



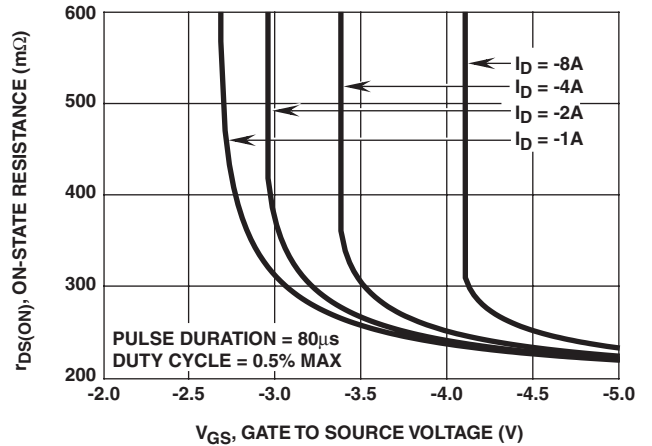
NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.  
**FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY**



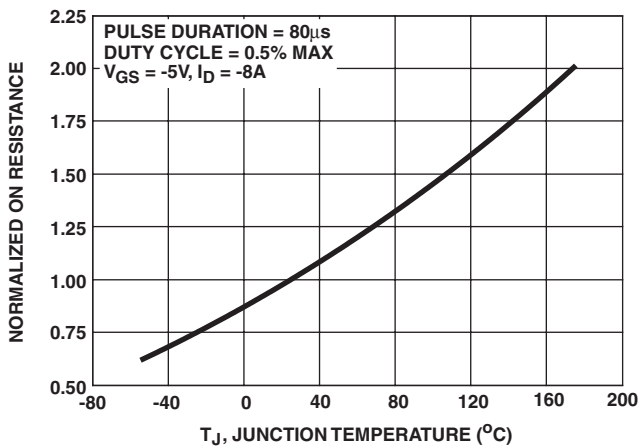
**FIGURE 7. SATURATION CHARACTERISTICS**



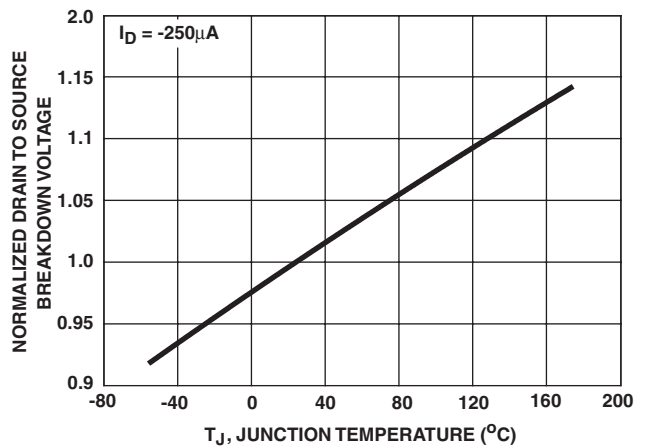
**FIGURE 8. TRANSFER CHARACTERISTICS**



**FIGURE 9. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT**



**FIGURE 10. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE**



**FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE**

**Typical Performance Curves** Unless Otherwise Specified

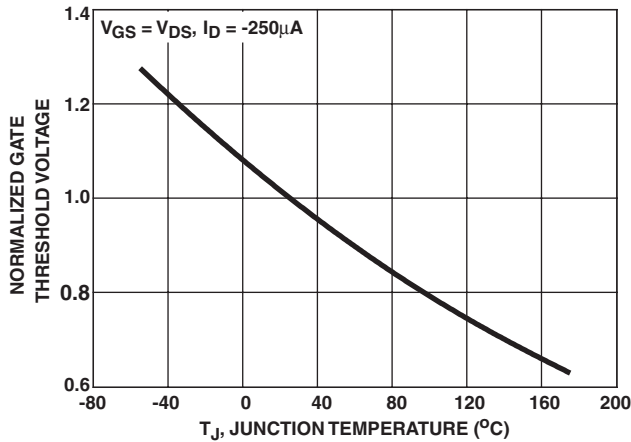


FIGURE 12. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

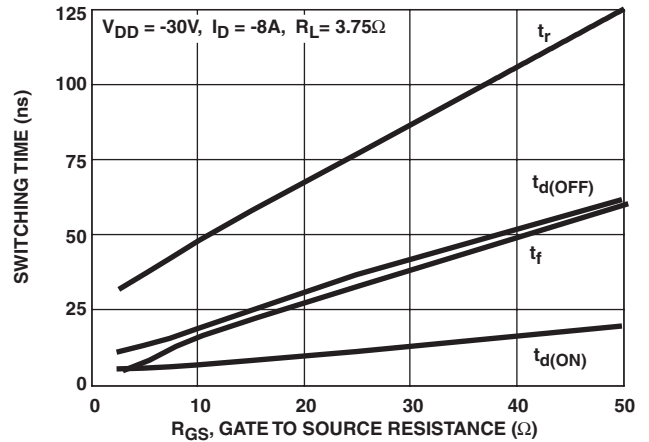
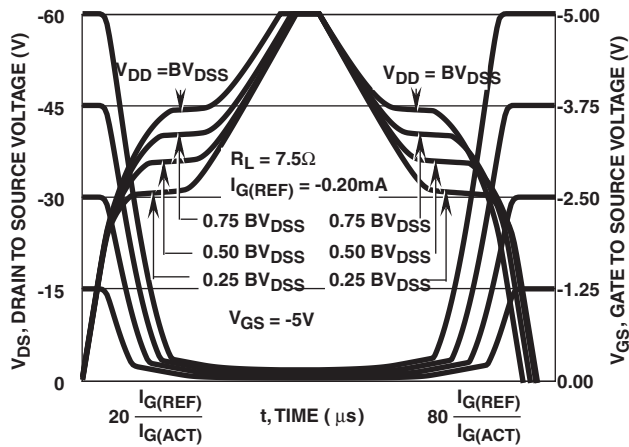


FIGURE 13. SWITCHING TIME AS A FUNCTION OF GATE RESISTANCE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 14. NORMALIZED SWITCHING WAVEFORMS FOR CONSTANT GATE CURRENT

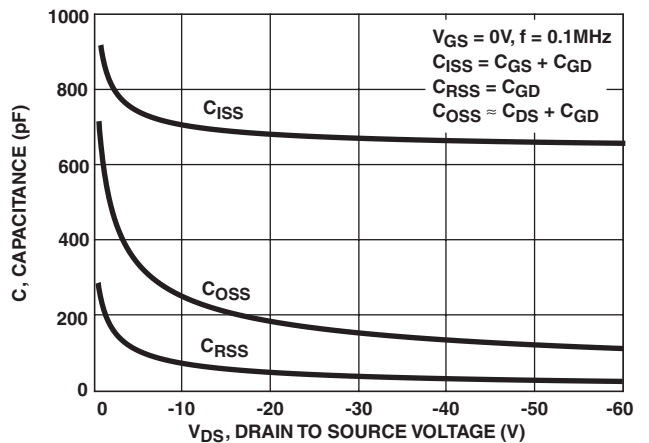


FIGURE 15. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

**Test Circuits and Waveforms**

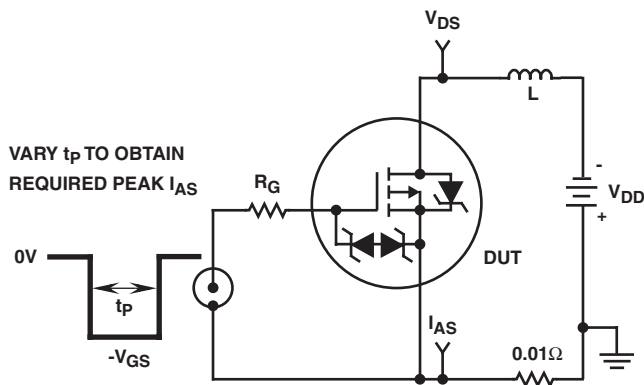


FIGURE 16. UNCLAMPED ENERGY TEST CIRCUIT

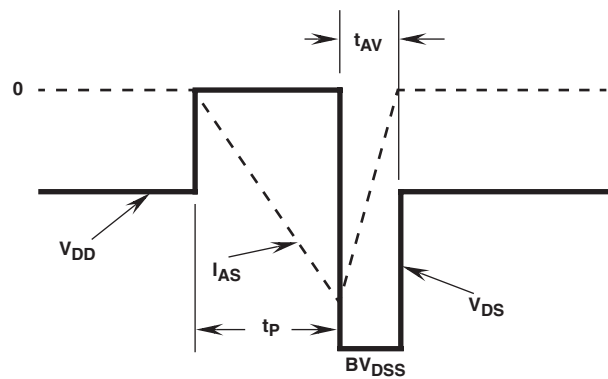


FIGURE 17. UNCLAMPED ENERGY WAVEFORMS

Test Circuits and Waveforms (Continued)

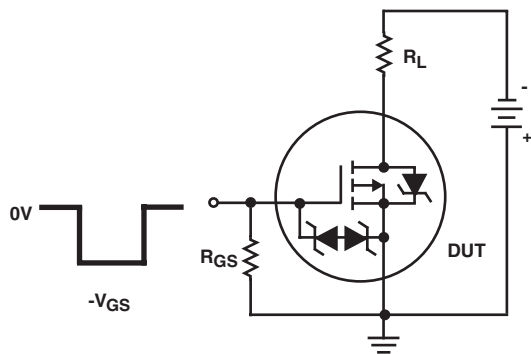


FIGURE 18. SWITCHING TIME TEST CIRCUIT

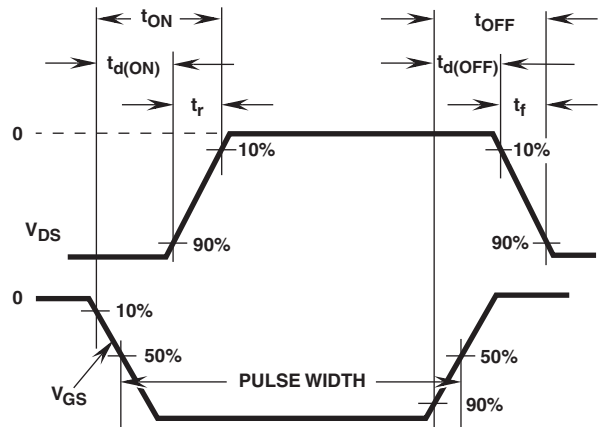


FIGURE 19. RESISTIVE SWITCHING WAVEFORMS

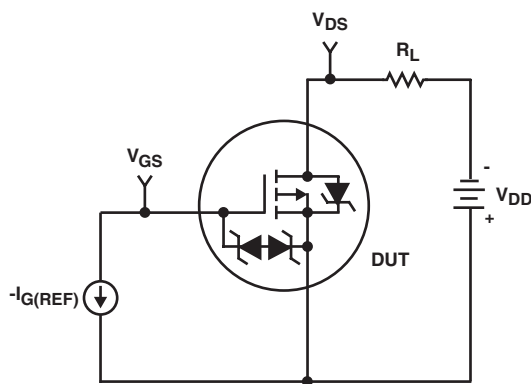


FIGURE 20. GATE CHARGE TEST CIRCUIT

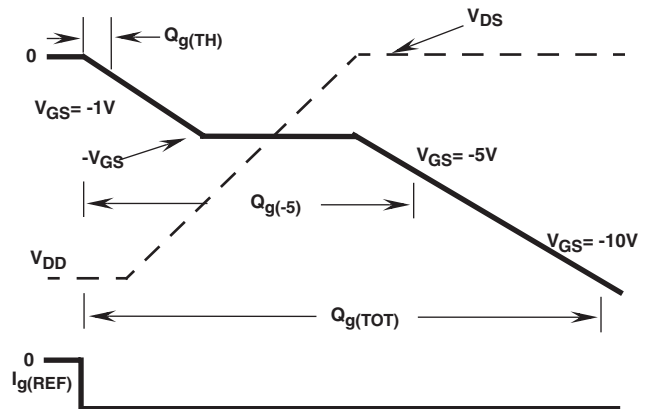


FIGURE 21. GATE CHARGE WAVEFORMS

# RFD8P06LE, RFD8P06LESM, RFP8P06LE

## PSpice Electrical Model

.SUBCKT RFD8P06LE 2 1 3 REV 7/29/96

CA 12 8 1.50e-9  
 CB 15 14 1.50e-9  
 CIN 6 8 6.30e-10

DBODY 5 7 DBDMOD  
 DBREAK 7 11 DBKMOD  
 DESD1 91 9 DESD1MOD  
 DESD2 91 7 DESD2MOD  
 DPLCAP 10 6 DPLCAPMOD

EBREAK 5 11 17 18 -67.9  
 EDS 14 8 5 8 1  
 EGS 13 8 6 8 1  
 ESG 5 10 8 6 1  
 EVTHRES 21 6 19 8 1  
 EVTEMP 6 20 18 22 1

IT 8 17 1

LDRAIN 2 5 1e-10  
 LGATE 1 9 2.92e-9  
 LSOURCE 3 7 2.92e-9

MSTRONG 16 6 8 8 MstrongMOD  
 MMED 16 6 8 8 MmedMOD  
 MWEAK 16 21 8 8 MweakMOD

RBREAK 17 18 RBKMOD 1  
 RDRAIN 50 16 RDSMOD 95e-3  
 RGATE 9 20 2.89  
 RIN 6 8 1e9  
 RSCL1 5 51 RSCLMOD 1e-6  
 RSCL2 5 50 1e3  
 RSOURCE 8 7 RSourceMOD 97e-3  
 RVTHRES 22 8 RVTHRESMOD 1  
 RVTEMP 18 19 RVTEMPMOD 1

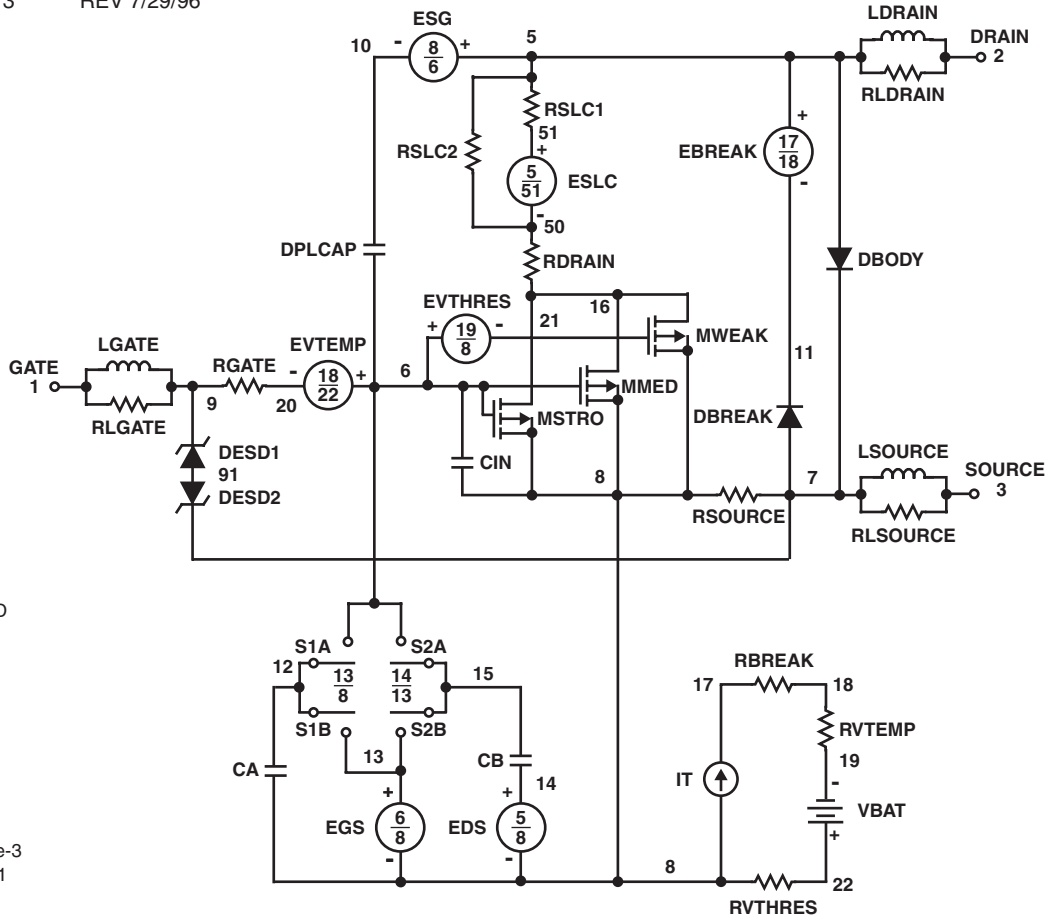
S1A 6 12 13 8 S1AMOD  
 S1B 13 12 13 8 S1BMOD  
 S2A 6 15 14 13 S2AMOD  
 S2B 13 15 14 13 S2BMOD

VBAT 22 19 DC 1

ESCL 51 50 VALUE={{(V(5,51)/ABS(V(5,51)))<sup>2</sup>\*(PWR(V(5,51)\*1e6/26,7))}}

.MODEL DBDMOD D (IS=2.5e-12 RS=4e-2 IKF=0.01 N=0.97 TIKF=0.012 TRS1=0.8e-4 TRS2=-5e-6 CJO=5.25e-10 VJ=0.75 M=0.41 TT=7.50e-8)  
 .MODEL DBKMOD D (IKF=5 N=0.75 RS=0.245 TRS1=1e-3 TRS2=1.6e-4)  
 .MODEL DESD1MOD D (BV=16.4 TBV1=-1.25e-3 TBV2=5.79e-7 RS=36 NBV=50 IBV=7e-6)  
 .MODEL DESD2MOD D (BV=16.2 TBV1=-8.3e-4 TBV2=8.9e-7 NBV=50 IBV=7e-6)  
 .MODEL DPLCAPMOD D (CJO=4.25e-10 IS=1e-30 N=10 VJ=0.499 M=0.561)  
 .MODEL MSTRONGMOD PMOS (VTO=-1.91 KP=11.55 IS=1e-30 N=10 TOX=1 L=1u W=1u)  
 .MODEL MMEDMOD PMOS (VTO=-1.51 KP=0.95 IS=1e-30 N=10 TOX=1 L=1u W=1u)  
 .MODEL MWEAKMOD PMOS (VTO=-1.18 KP=0.03 IS=1e-30 N=10 TOX=1 L=1u W=1u)  
 .MODEL RBKMOD RES (TC1=1.045e-3 TC2=-3.5e-7)  
 .MODEL RDSMOD RES (TC1=0.92e-2 TC2=1.55e-5)  
 .MODEL RSourceMOD RES (TC1=2e-3 TC2=0.5e-6)  
 .MODEL RSCLMOD RES (TC1=2e-3 TC2=0)  
 .MODEL RVTHRESMOD RES (TC1=-2.5e-3 TC2=0)  
 .MODEL RVTEMPMOD RES (TC1=-1.55e-3 TC2=7.5e-6)  
 .MODEL S1AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=5.25 VOFF=1.75)  
 .MODEL S1BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=1.75 VOFF=5.25)  
 .MODEL S2AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=0.5 VOFF=-0.5)  
 .MODEL S2BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-0.5 VOFF=0.5)  
 .ENDS

NOTE: For further discussion of the PSpice model consult A New PSpice Sub-circuit for the Power MOSFET Featuring Global Temperature Options; authored by William J. Hepp and C. Frank Wheatley.



**PSpice Thermal Model**

REV 7/29/96

RFP8P06LE

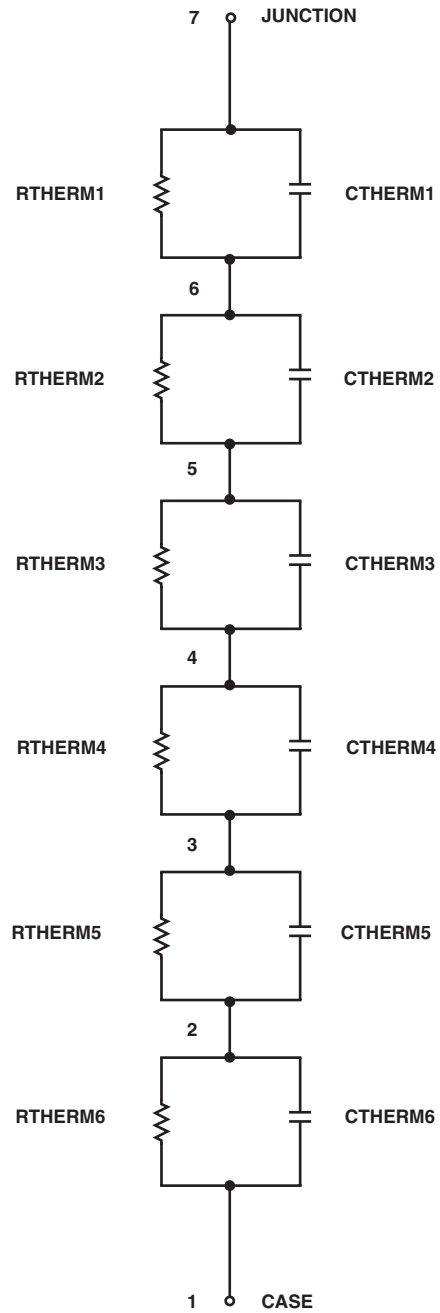
CTHERM1 7 6 1.3e-4  
 CTHERM2 6 5 4.5e-4  
 CTHERM3 5 4 1e-3  
 CTHERM4 4 3 2e-3  
 CTHERM5 3 2 1.5e-2  
 CTHERM6 2 1 0.55

RTHERM1 7 6 3.0e-2  
 RTHERM2 6 5 5.0e-2  
 RTHERM3 5 4 0.1  
 RTHERM4 4 3 1.15  
 RTHERM5 3 2 1.20  
 RTHERM6 2 1 0.55

RFD8P06LE, RFD8P06LESM

CTHERM1 7 6 1.3e-4  
 CTHERM2 6 5 4.5e-4  
 CTHERM3 5 4 1e-3  
 CTHERM4 4 3 2e-3  
 CTHERM5 3 2 1.5e-2  
 CTHERM6 2 1 0.12

RTHERM1 7 6 3.0e-2  
 RTHERM2 6 5 5.0e-2  
 RTHERM3 5 4 0.1  
 RTHERM4 4 3 1.15  
 RTHERM5 3 2 1.20  
 RTHERM6 2 1 0.55





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Bottomless <sup>TM</sup>	FAST <sub>r</sub> <sup>TM</sup>	OPTOPLANAR <sup>TM</sup>	STAR*POWER <sup>TM</sup>	
CoolFET <sup>TM</sup>	FRFET <sup>TM</sup>	PACMAN <sup>TM</sup>	Stealth <sup>TM</sup>	
CROSSVOLT <sup>TM</sup>	GlobalOptoisolator <sup>TM</sup>	POP <sup>TM</sup>	SuperSOT <sup>TM</sup> -3	
DenseTrench <sup>TM</sup>	GTO <sup>TM</sup>	Power247 <sup>TM</sup>	SuperSOT <sup>TM</sup> -6	
DOMET <sup>TM</sup>	HiSeC <sup>TM</sup>	PowerTrench <sup>®</sup>	SuperSOT <sup>TM</sup> -8	
EcoSPARK <sup>TM</sup>	ISOPLANAR <sup>TM</sup>	QFET <sup>TM</sup>	SyncFET <sup>TM</sup>	
E <sup>2</sup> CMOS <sup>TM</sup>	LittleFET <sup>TM</sup>	QST <sup>TM</sup>	TinyLogic <sup>TM</sup>	
EnSigna <sup>TM</sup>	MicroFET <sup>TM</sup>	QT Optoelectronics <sup>TM</sup>	TruTranslation <sup>TM</sup>	
FACT <sup>TM</sup>	MicroPak <sup>TM</sup>	Quiet Series <sup>TM</sup>	UHC <sup>TM</sup>	
FACT Quiet Series <sup>TM</sup>	MICROWIRE <sup>TM</sup>	SILENT SWITCHER <sup>®</sup>	UltraFET <sup>®</sup>	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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